

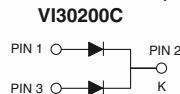
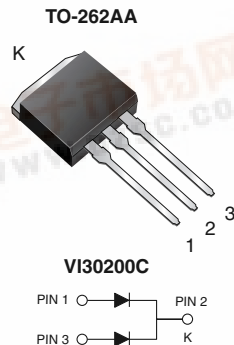
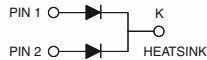
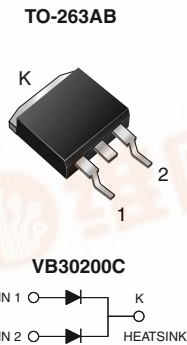
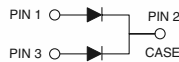
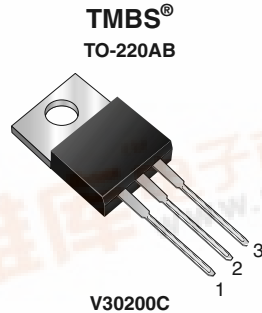


V30200C, VB30200C & VI30200C

Vishay General Semiconductor

Dual High-Voltage Trench MOS Barrier Schottky Rectifier

Ultra Low $V_F = 0.526$ V at $I_F = 5$ A



FEATURES

- Trench MOS Schottky technology
- Low forward voltage drop, low power losses
- High efficiency operation
- Low thermal resistance
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for TO-263AB package)
- Solder dip 260 °C, 40 s (for TO-220AB and TO-262AA package)
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



RoHS COMPLIANT

TYPICAL APPLICATIONS

For use in high frequency inverters, switching power supplies, freewheeling diodes, OR-ing diode, dc-to-dc converters and reverse battery protection.

MECHANICAL DATA

Case: TO-220AB, TO-263AB and TO-262AA

Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD22-B102

E3 suffix for consumer grade, meets JESD 201 class 1A whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

PRIMARY CHARACTERISTICS

$I_{F(AV)}$	2 x 15 A
V_{RRM}	200 V
I_{FSM}	250 A
V_F at $I_F = 15$ A	0.648 V
T_J max.	150 °C

MAXIMUM RATINGS ($T_A = 25$ °C unless otherwise noted)

PARAMETER	SYMBOL	V30200C	VB30200C	VI30200C	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}		200		V
Maximum average forward rectified current per device (Fig. 1)	$I_{F(AV)}$		30		A
			15		
Peak forward surge current 10 ms single half sine-wave superimposed on rated load per diode	I_{FSM}		250		A
Non-repetitive avalanche energy at $I_{AS} = 2.0$ A, $T_J = 25$ °C	E_{AS}		100		mJ
Peak repetitive reverse current at $t_p = 2$ μs, 1 kHz per diode	I_{RRM}		1.0		A
Voltage rate of change (rated V_R)	dV/dt		10 000		V/μs
Operating junction and storage temperature range	T_J, T_{STG}		- 40 to + 150		°C



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ELECTRICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)						
PARAMETER	TEST CONDITIONS		SYMBOL	TYP.	MAX.	UNIT
Breakdown voltage	$I_R = 10\text{ mA}$	$T_J = 25\text{ }^{\circ}\text{C}$	V_{BR}	205 (minimum)	-	V
Instantaneous forward voltage per diode ⁽¹⁾	$I_F = 5\text{ A}$	$T_J = 25\text{ }^{\circ}\text{C}$	V_F	0.691	-	V
	$I_F = 10\text{ A}$			0.770	-	
	$I_F = 15\text{ A}$			0.841	1.10	
	$I_F = 5\text{ A}$	$T_J = 125\text{ }^{\circ}\text{C}$		0.526	-	
Reverse current per diode ⁽²⁾	$V_R = 180\text{ V}$	$T_J = 25\text{ }^{\circ}\text{C}$	I_R	2.4	-	μA
	$V_R = 180\text{ V}$	$T_J = 125\text{ }^{\circ}\text{C}$		3.8	-	mA
	$V_R = 200\text{ V}$	$T_J = 25\text{ }^{\circ}\text{C}$		5.3	160	μA
	$V_R = 200\text{ V}$	$T_J = 125\text{ }^{\circ}\text{C}$		6.0	12	mA

Notes:

(1) Pulse test: 300 μs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width $\leq 40\text{ ms}$

THERMAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)					
PARAMETER	SYMBOL	V30200C	VB30200C	VI30200C	UNIT
Typical thermal resistance per diode	$R_{\theta JC}$	2.0			$^{\circ}\text{C/W}$

ORDERING INFORMATION (Example)					
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
TO-220AB	V30200C-E3/4W	2.248	4W	50/tube	Tube
TO-263AB	VB30200C-E3/4W	1.39	4W	50/tube	Tube
TO-263AB	VB30200C-E3/8W	1.39	8W	800/reel	Tape and reel
TO-262AA	VI30200C-E3/4W	1.46	4W	50/tube	Tube

RATINGS AND CHARACTERISTICS CURVES

($T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)

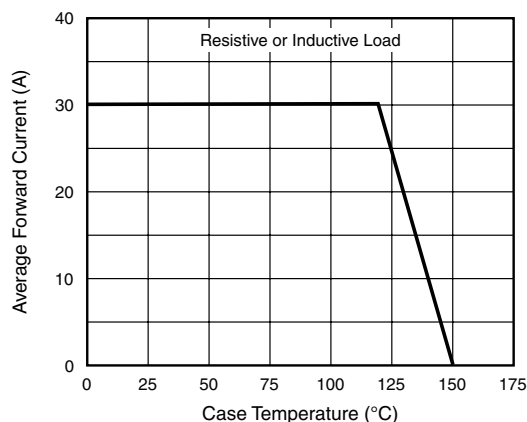


Figure 1. Forward Derating Curve

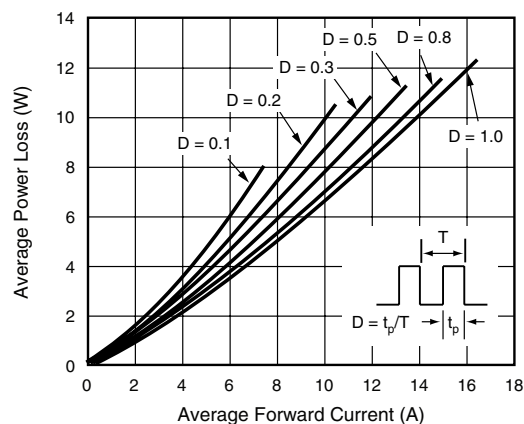


Figure 2. Forward Power Loss Characteristics Per Diode



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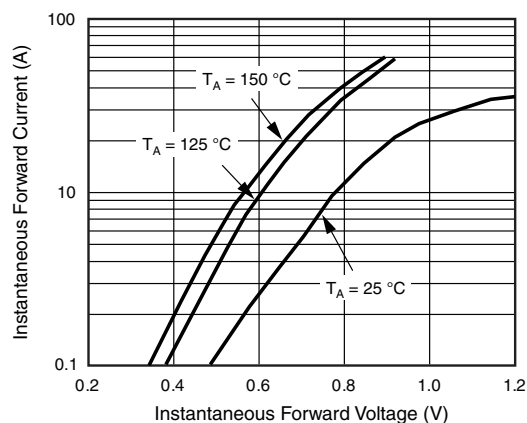


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

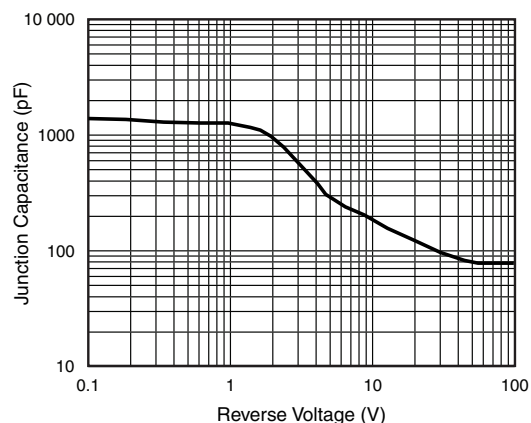


Figure 5. Typical Junction Capacitance Per Diode

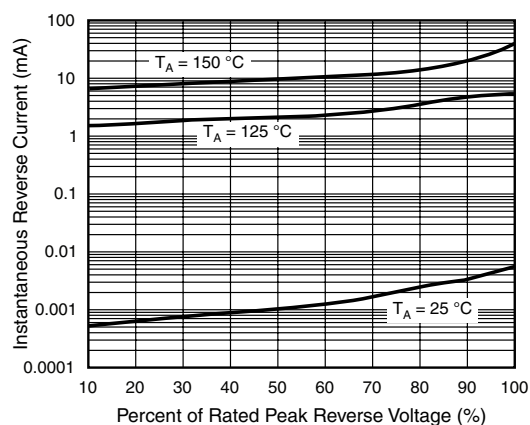


Figure 4. Typical Reverse Characteristics Per Diode

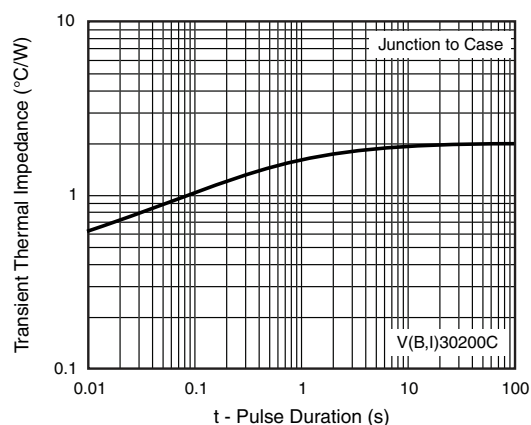


Figure 6. Typical Transient Thermal Impedance Per Diode

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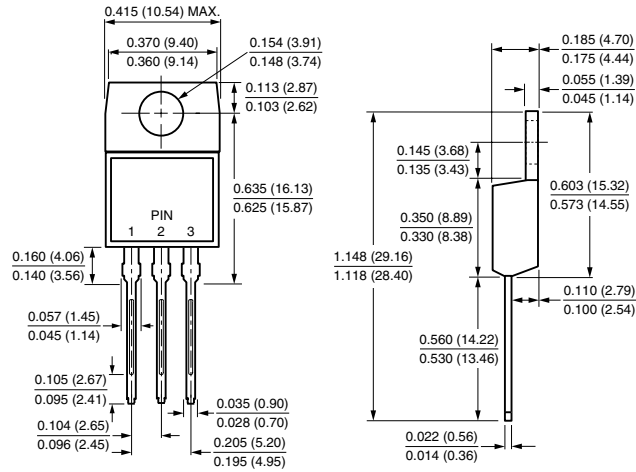
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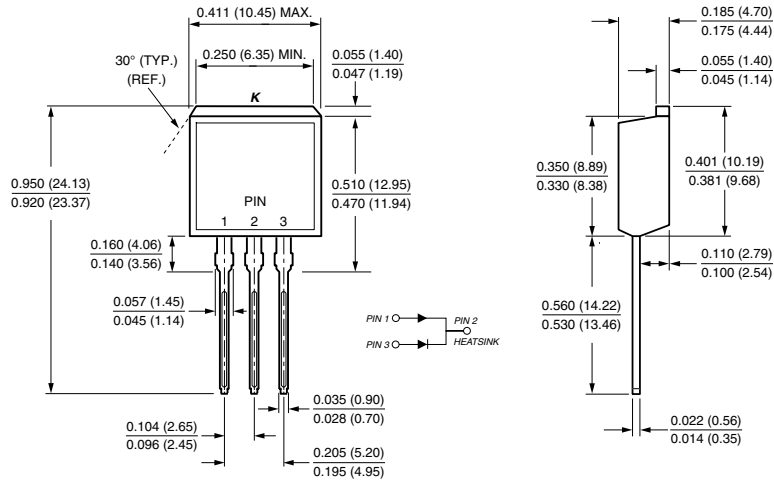


PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

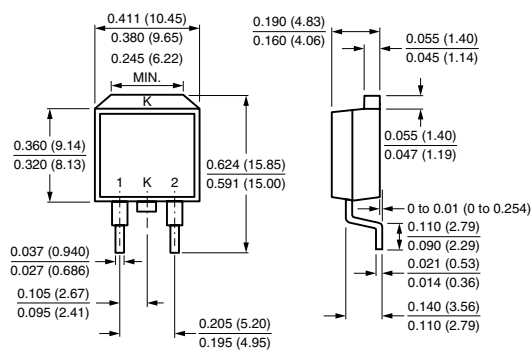
TO-220AB



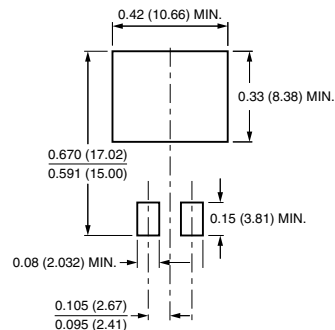
TO-262AA



TO-263AB



Mounting Pad Layout





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